

/ Descriptions

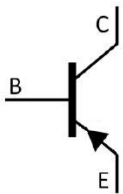
WR0<50 P SQS Silicon PNP transistor in a TO-92LM Plastic Package.

/ Features

NWF655 :
Complementary pair with KTC3227.

δ

General purpose application.



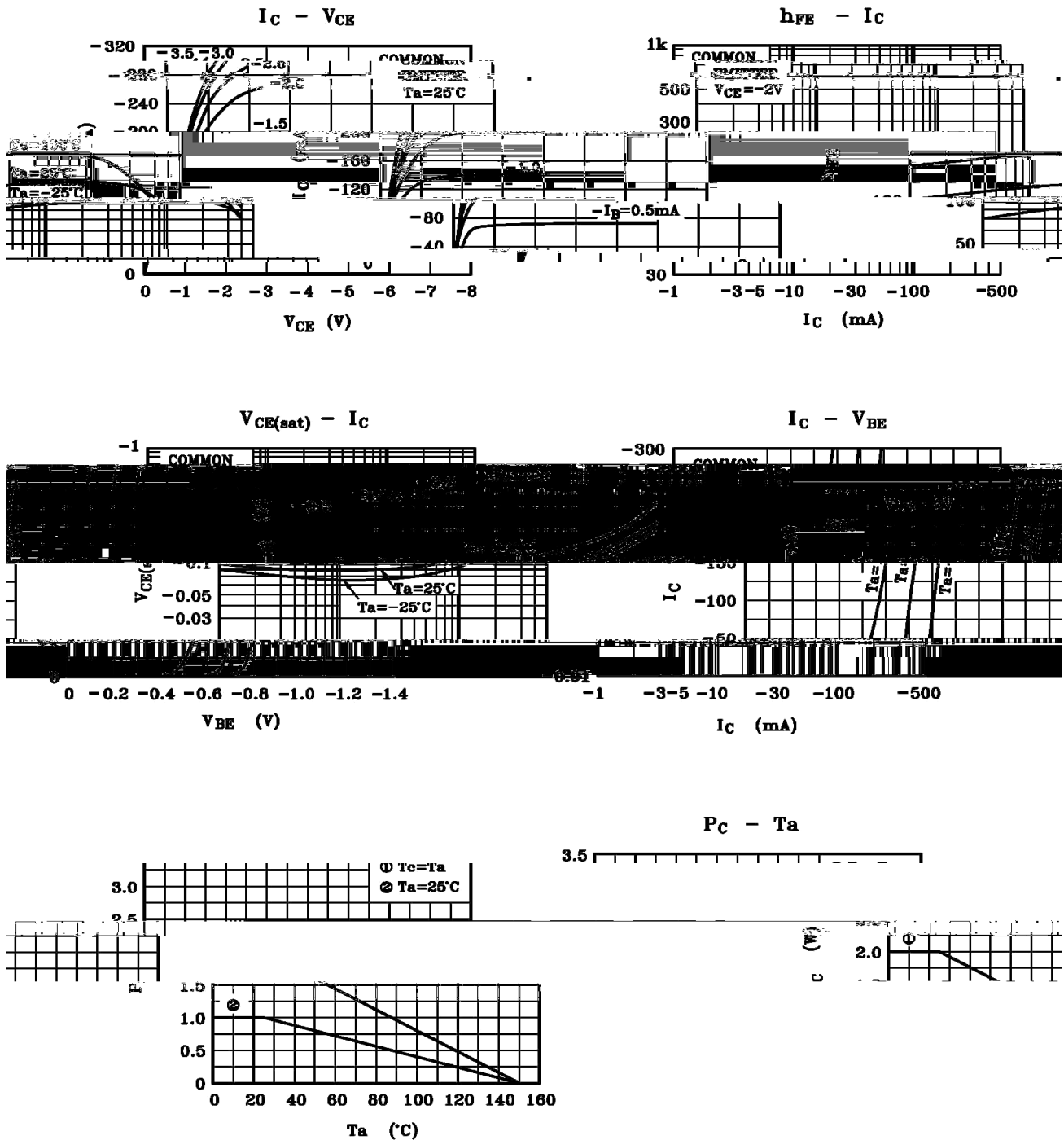
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-400	mA
Emitter Current - Continuous	I_E	400	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -5.0mA$ $I_B = 0$	-80			V

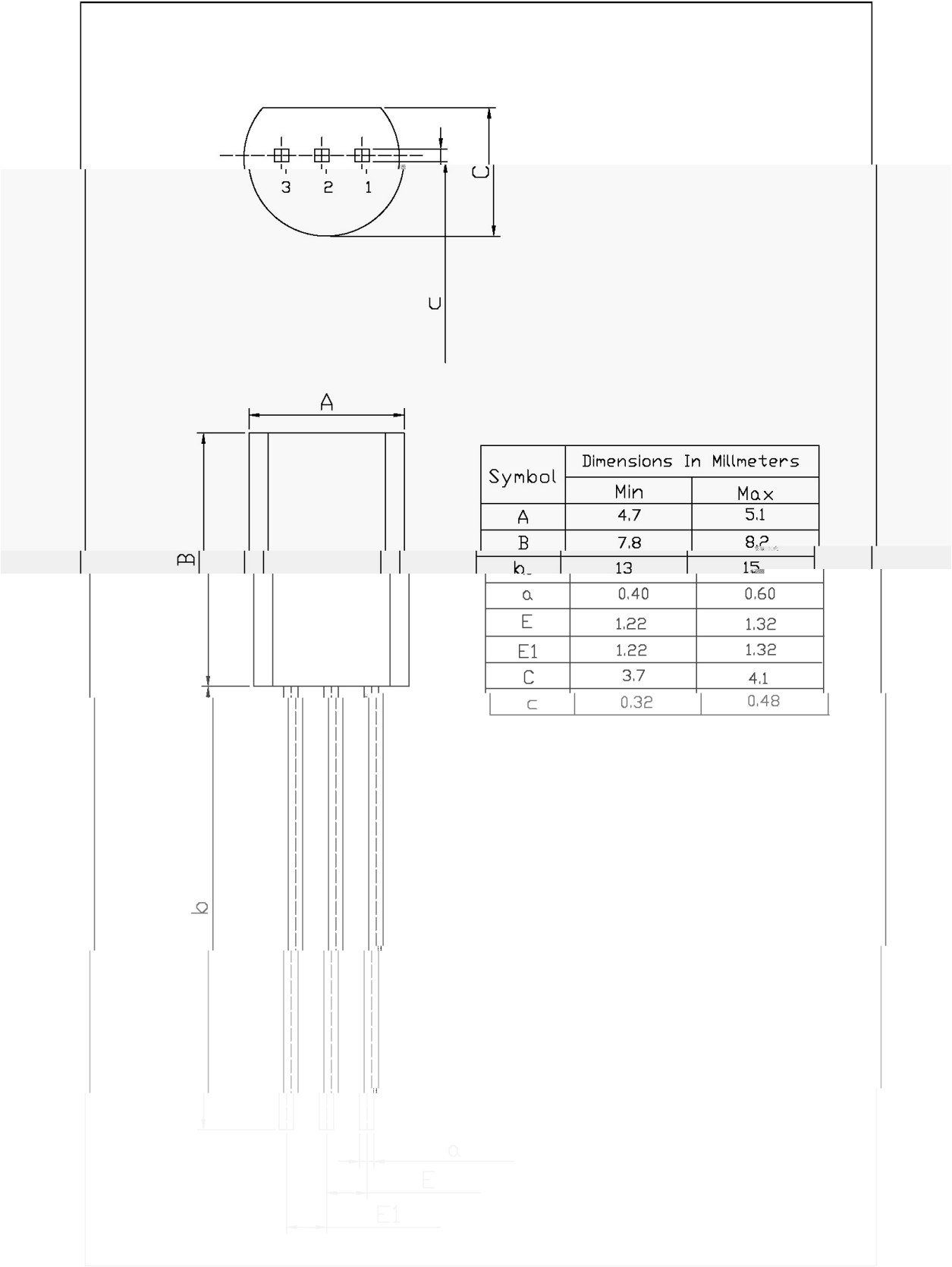
/ Electrical Characteristic Curve



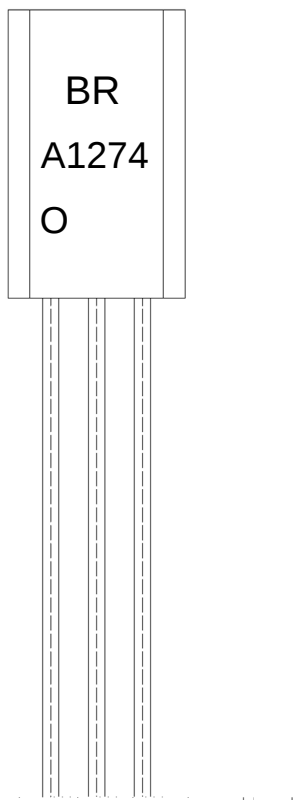
/ Package Dimensions

T0-92LM

Unit: mm



/ Marking Instructions



EU:

D45 : 7

R: k_{IH}

Note:

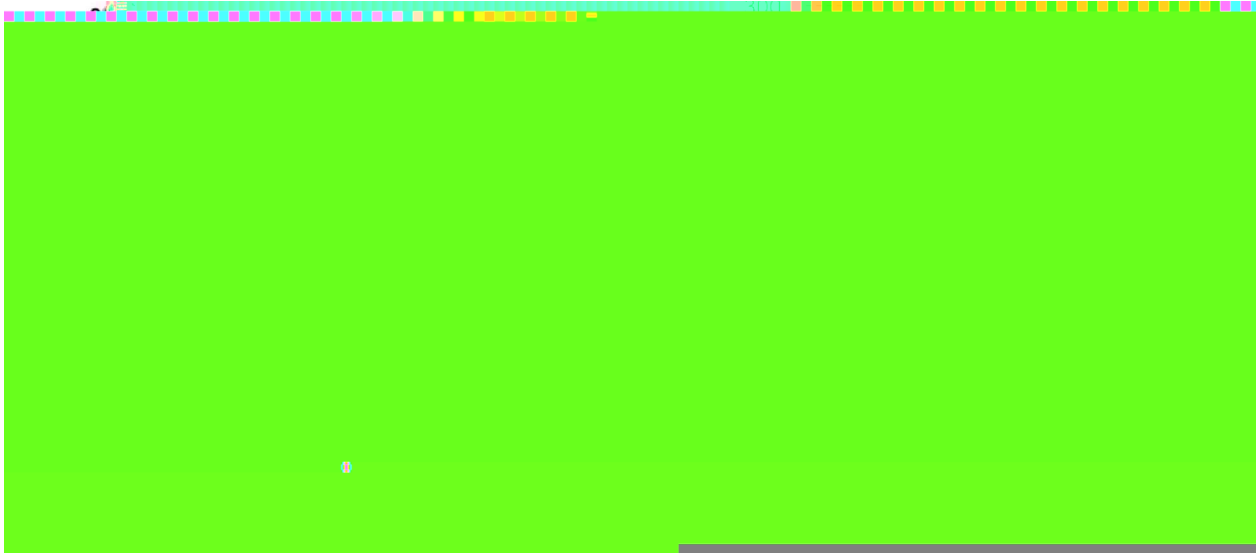
BR: Company Code.

A1274: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1 25 150 $\frac{3}{8}$ 60 90sec;
- 2 255 $\pm$ 5 $\frac{3}{8}$ 5 $\pm$ 0.5sec;
- 3 2 10 $\frac{3}{8}$ /sec.

- 1.Preheating:25~150 $\frac{3}{8}$, Time:60~90sec.
- 2.Peak Temp.:255 $\pm$ 5 $\frac{3}{8}$, Duration:5 $\pm$ 0.5sec.
3. Cooling Speed: 2~10 $\frac{3}{8}$ /sec.

/ Resistance to Soldering Heat Test Conditions

270 $\pm$ 5 $\frac{3}{8}$ 10 $\pm$ 1 sec. Temp.:270 $\pm$ 5 $\frac{3}{8}$ Time:10 $\pm$ 1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension		(unit mm3)

/ Notices